

HiPerFET™

Power MOSFETs

IXFN44N50U2

IXFN44N50U3

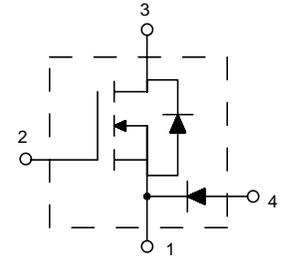
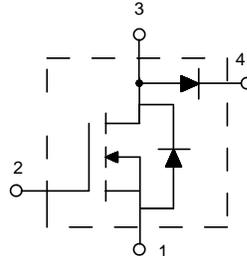
V_{DSS}	I_D (cont)	$R_{DS(on)}$	t_{rr}
500 V	44 A	0.12 Ω	35 ns
500 V	48 A	0.10 Ω	35 ns

IXFN48N50U2

IXFN48N50U3

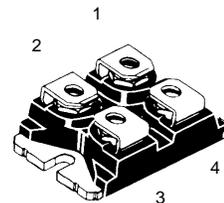
Buck & Boost Configurations for PFC & Motor Control Circuits

Preliminary data



Symbol	Test Conditions	Maximum Ratings			
HiPerFET MOSFET	V_{DSS}	$T_J = 25^\circ\text{C}$ to 150°C	500	V	
	V_{DGR}	$T_J = 25^\circ\text{C}$ to 150°C ; $R_{GS} = 1\text{ M}\Omega$	500	V	
	V_{GS}	Continuous	± 20	V	
	V_{GSM}	Transient	± 30	V	
	I_{D25}	$T_C = 25^\circ\text{C}$	44N50	44	A
			48N50	48	A
	I_{DM}	$T_C = 25^\circ\text{C}$, pulse width limited by max. T_{JM}	44N50	176	A
			48N50	192	A
	I_{AR}	$T_C = 25^\circ\text{C}$	24	A	
	E_{AR}	Repetitive	30	mJ	
dv/dt	$I_S \leq I_{DM}$, $-di/dt \leq 100\text{ A}/\mu\text{s}$, $V_{DD} \leq V_{DSS}$, $T_J \leq 150^\circ\text{C}$, $R_G = 2\ \Omega$	5	V/ns		
P_D	$T_C = 25^\circ\text{C}$	520	W		
DIODE	V_{RRM}		600	V	
	I_{FAVM}	$T_C = 70^\circ\text{C}$; rectangular, $d = 0.5$	60	A	
	I_{FRM}	$tp < 10\ \mu\text{s}$; pulse width limited by T_J	800	A	
	P_D	$T_C = 25^\circ\text{C}$	180	W	
CASE	T_J		-40 ... +150	$^\circ\text{C}$	
	T_{JM}		150	$^\circ\text{C}$	
	T_{stg}		-40 ... +150	$^\circ\text{C}$	
	V_{ISOL}	50/60 Hz, RMS	$t = 1\text{ min}$	2500	V~
		$I_{ISOL} \leq 1\text{ mA}$	$t = 1\text{ s}$	3000	V~
M_d	Mounting torque		1.5/13	Nm/lb.in.	
	Terminal connection torque (M4)		1.5/13	Nm/lb.in.	
Weight			30	g	

miniBLOC, SOT-227 B



Features

- Popular Buck & Boost circuit topologies
- International standard package miniBLOC SOT-227B
- Aluminium nitride isolation - high power dissipation
- Isolation voltage 3000 V~
- Low $R_{DS(on)}$ HDMOS™ process
- Rugged polysilicon gate cell structure
- Low drain-to-case capacitance (<60 pF) - reduced RFI
- Ultra-fast FRED diode with soft reverse recovery

Applications

- Power factor controls and buck regulators
- DC servo and robotic drives
- DC choppers
- Switch reluctance motor controls

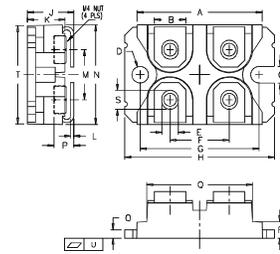
Advantages

- Easy to mount with 2 screws
- Space savings
- Tightly coupled FRED

Symbol	Test Conditions	Characteristic Values		
		(T _J = 25°C, unless otherwise specified)		
		min.	typ.	max.
V _{DSS}	V _{GS} = 0 V, I _D = 1 mA	500		V
V _{GS(th)}	V _{DS} = V _{GS} , I _D = 8 mA	2		4 V
I _{GSS}	V _{GS} = ±20 V _{DC} , V _{DS} = 0			±200 nA
I _{DSS}	V _{DS} = 0.8 V _{DSS} V _{GS} = 0 V	T _J = 25°C T _J = 125°C		400 μA 2 mA
R _{DS(on)}	V _{GS} = 10 V, I _D = 0.5 I _{D25}	44N50 48N50		0.12 Ω 0.10 Ω
Pulse test, t ≤ 300 μs, duty cycle δ ≤ 2 %				

Symbol	Test Conditions	Characteristic Values		
		(T _J = 25°C, unless otherwise specified)		
		min.	typ.	max.
g _{fs}	V _{DS} = 10 V, I _D = 0.5 I _{D25} , pulse test	22	42	S
C _{iss}	V _{GS} = 0 V, V _{DS} = 25 V, f = 1 MHz		8400	pF
C _{oss}			900	pF
C _{rss}			280	pF
t _{d(on)}	V _{GS} = 10 V, V _{DS} = 0.5 V _{DSS} , I _D = 0.5 I _{D25} R _G = 1 Ω (External)		30	ns
t _r			60	ns
t _{d(off)}			100	ns
t _f			30	ns
Q _{g(on)}	V _{GS} = 10 V, V _{DS} = 0.5 V _{DSS} , I _D = 0.5 I _{D25}		270	nC
Q _{gs}			60	nC
Q _{gd}			135	nC
R _{thJC}			0.24	K/W
R _{thCK}			0.05	K/W

Symbol	Test Conditions	Characteristic Values		
		(T _J = 25°C, unless otherwise specified)		
		min.	typ.	max.
I _R	T _J = 25°C; V _R = V _{R_{RM}} V _R = 0.8V _{R_{RM}} T _J = 125°C; V _R = 0.8V _{R_{RM}}			200 μA
				100 μA
				14 mA
V _F	I _F = 70A, V _{GS} = 0 V, T _J = 150°C Pulse test, t ≤ 300 μs, duty cycle δ ≤ 2 % T _J = 25°C			1.5 V
				1.8 V
t _{rr}	I _F = 1A, di/dt = -200 A/μs, V _R = 30 V, T _J = 25°C		35	50 ns
I _{RM}	I _F = 60A, di/dt = -480 A/μs, V _R = 350 V, T _J = 100°C		19	21 A
R _{thJC}				0.7 K/W
R _{thJK}			0.05	K/W

miniBLOC, SOT-227 B


M4 screws (4x) supplied

Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	31.50	31.88	1.240	1.255
B	7.80	8.20	0.307	0.323
C	4.09	4.29	0.161	0.169
D	4.09	4.29	0.161	0.169
E	4.09	4.29	0.161	0.169
F	14.91	15.11	0.587	0.595
G	30.12	30.30	1.186	1.193
H	38.00	38.23	1.496	1.505
J	11.68	12.22	0.460	0.481
K	8.92	9.60	0.351	0.378
L	0.76	0.84	0.030	0.033
M	12.60	12.85	0.496	0.506
N	25.15	25.42	0.990	1.001
O	1.98	2.13	0.078	0.084
P	4.95	5.97	0.195	0.235
Q	26.54	26.90	1.045	1.059
R	3.94	4.42	0.155	0.174
S	4.72	4.85	0.186	0.191
T	24.59	25.07	0.968	0.987
U	-0.05	0.1	-0.002	0.004

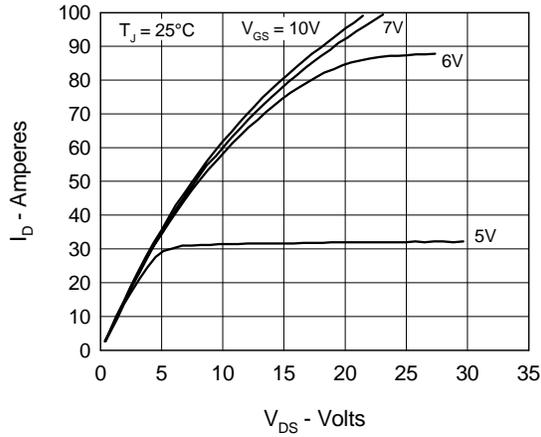
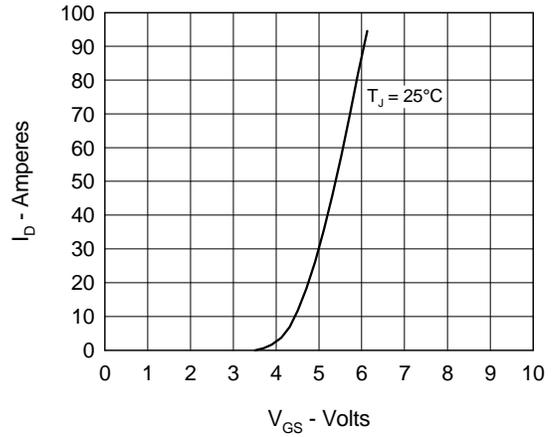
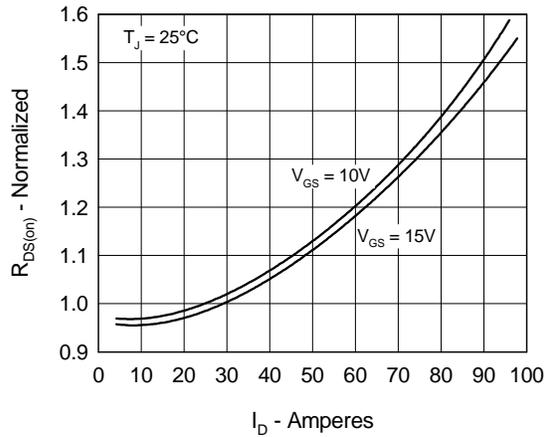
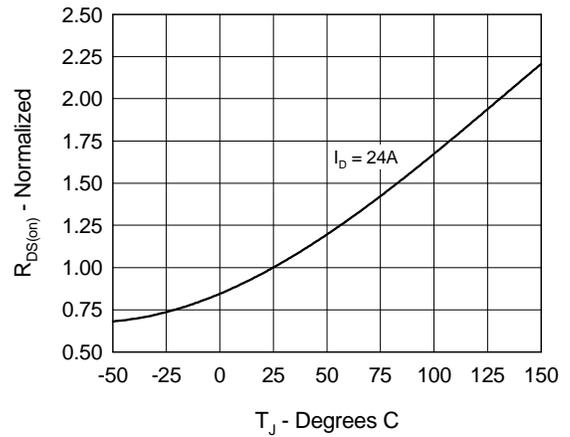
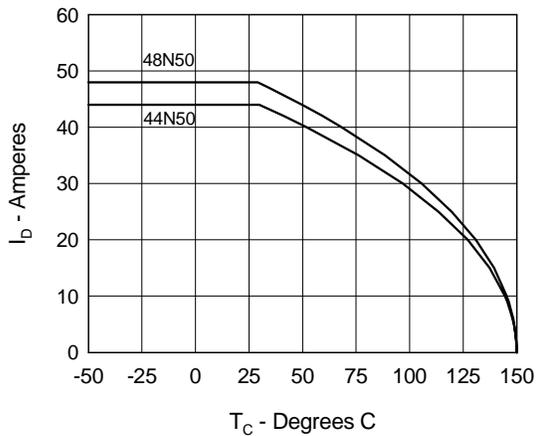
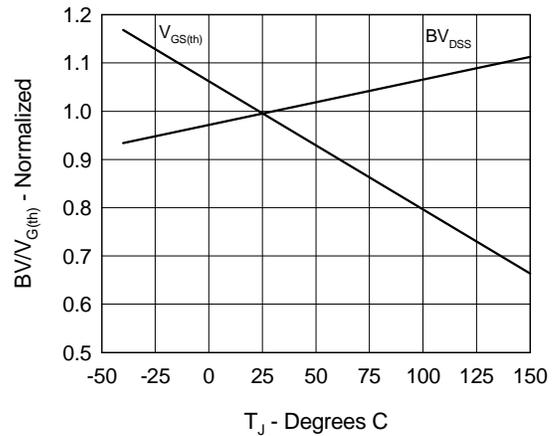
Fig.1 Output Characteristics

Fig.2 Input Admittance

Fig.3 $R_{DS(on)}$ vs. Drain Current

Fig.4 Temperature Dependence of Drain to Source Resistance

Fig.5 Drain Current vs. Case Temperature

Fig.6 Temperature Dependence of Breakdown and Threshold Voltage


Fig.7 Gate Charge Characteristic Curve

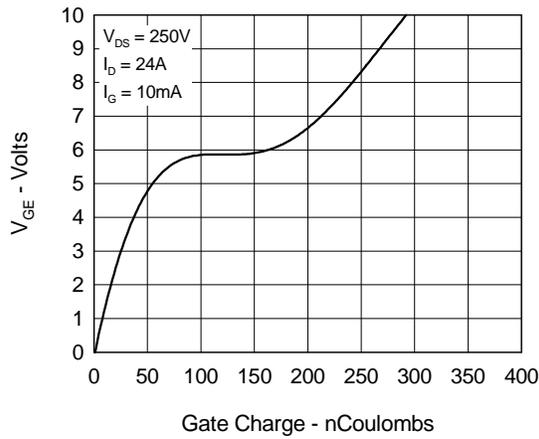


Fig.8 Capacitance Curves

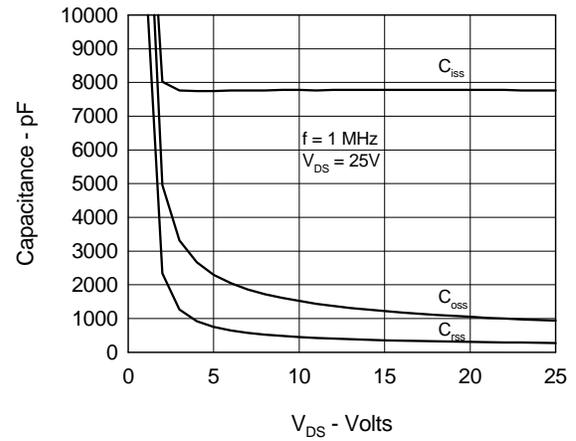


Fig.9 Source Current vs. Source to Drain Voltage

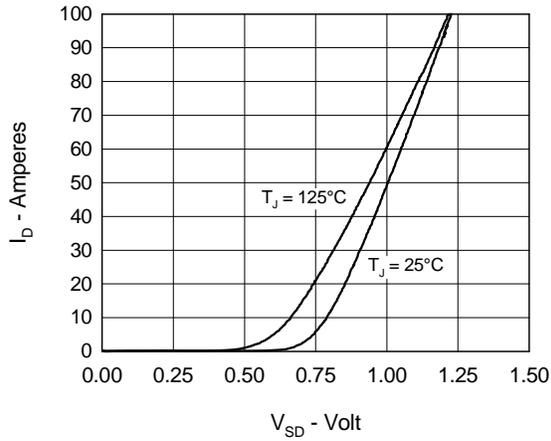
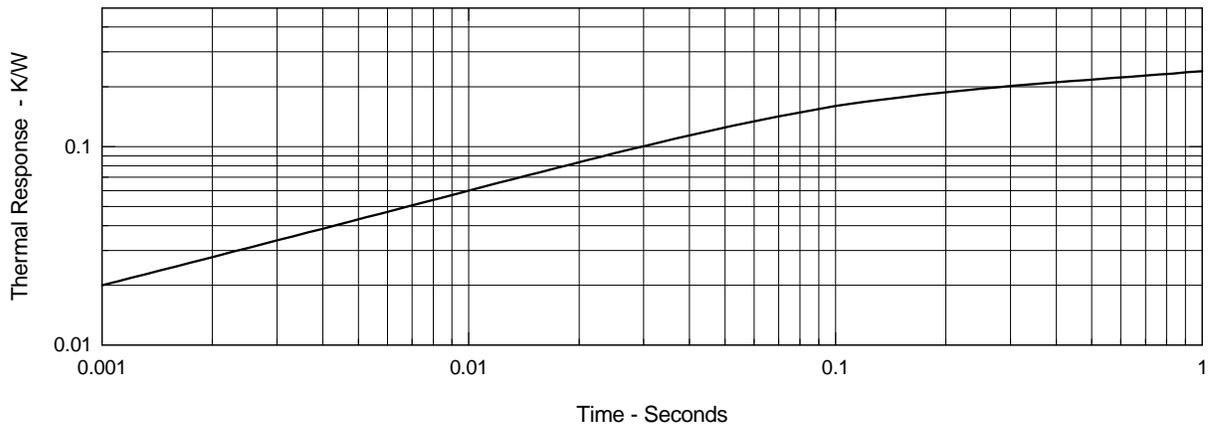


Fig.10 Transient Thermal Impedance



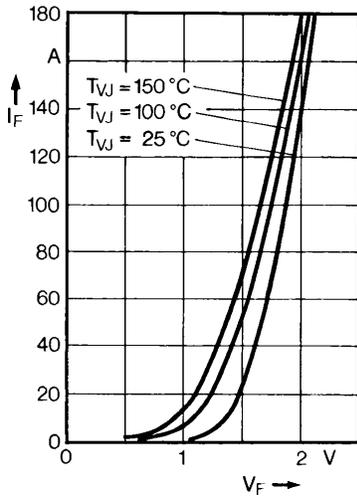


Fig. 11. Forward voltage drop.

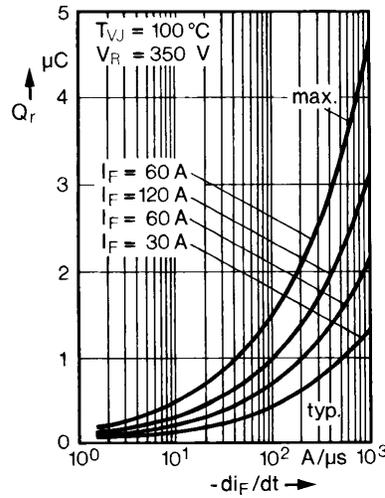


Fig. 12. Recovery charge versus $-di_F/dt$.

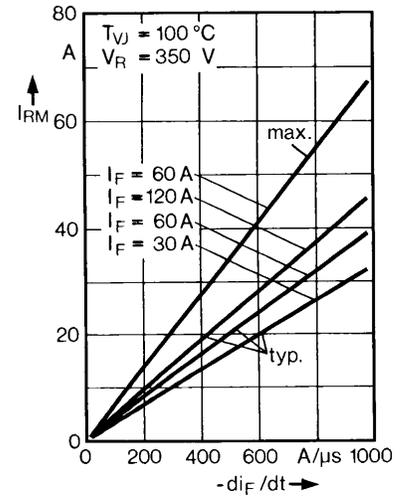


Fig. 13. Peak reverse current vs. $-di_F/dt$.

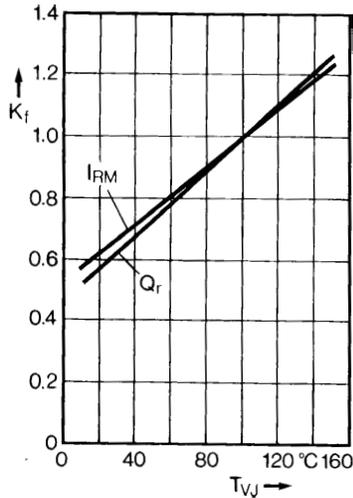


Fig. 14. Dynamic parameters versus junction temperature.

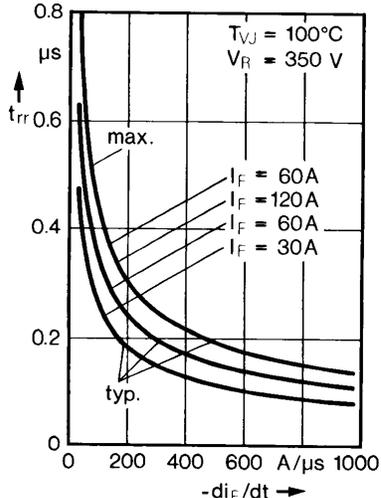


Fig. 15. Recovery time versus $-di_F/dt$.

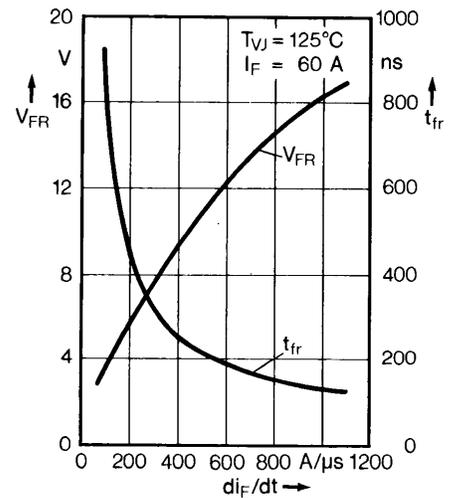


Fig. 16. Peak forward voltage and forward recovery time vs. di_F/dt .

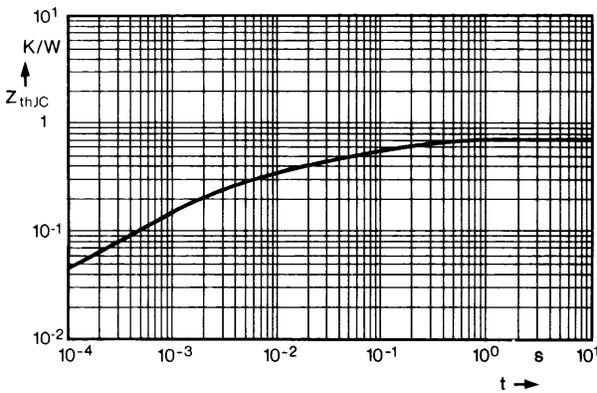


Fig. 17. Transient thermal impedance junction to case.